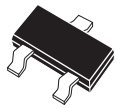
CMPD1001
CMPD1001A
CMPD1001S

HIGH CURRENT
SWITCHING DIODE



SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION:
The Central Semiconductor CMPD1001 series types are silicon switching diodes manufactured by the epitaxial planar process, designed for applications requiring high current capability.

The following configurations are available:

CMPD1001	SINGLE	**MARKING CODE: L20**
CMPD1001S	DUAL, IN SERIES	**MARKING CODE: L21**
CMPD1001A	DUAL, COMMON ANODE	**MARKING CODE: L22**

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	90	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	600	mA
Peak Repetitive Reverse Current	I_{RRM}	600	mA
Forward Surge Current, tp=1.0 μs	I_{FSM}	6.0	A
Forward Surge Current, tp=1.0 s	I_{FSM}	1.0	A
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
BV_R	I_R=100μA	90		V
I_R	V_R=90V		100	nA
I_R	V_R=90V, T_A=150°C		100	μA
V_F	I_F=10mA		0.75	V
V_F	I_F=50mA		0.84	V
V_F	I_F=100mA		0.90	V
V_F	I_F=200mA		1.00	V
V_F	I_F=400mA		1.25	V
C_T	V_R=0V, f=1.0 MHz		35	pF
t_{rr}	I_R=I_F=30mA, Rec. to 3.0mA, R_L=100Ω		50	ns

R4 (13-November 2002)

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CMPD1001
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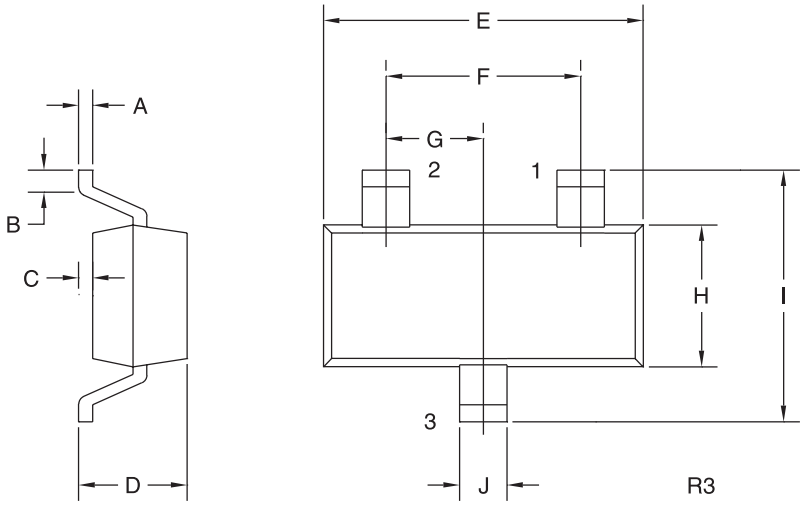
HIGH CURRENT
SWITCHING DIODE

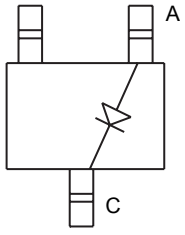
SOT-23 CASE - MECHANICAL OUTLINE



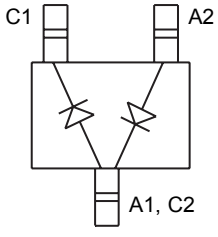
DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

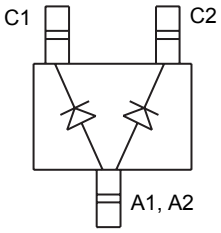
NO CONNECTION



CMPD1001
MARKING CODE: L20



CMPD1001S
MARKING CODE: L21



CMPD1001A
MARKING CODE: L22

R4 (13-November 2002)